MICRO ELECTRONICS

MI51TA
MIB51TA
INFRARED EMITTING DIODE

DESCRIPTION

MI51TA & MIB51TA are GaAlAs infrared emitting diode molded T-1 3/4 standard 5mm diameter clear plastic package, with the lensing effect of the package, and MIB51TA with cup type leadframe.

ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	180mW
Operating Temperature Range	-25 to +85℃
Lead Soldering Temperature (1/16" from body)	260℃ for 5 sec.

** Pulse Width = 10 μs, Duty Ratio = 0.01.*

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25℃)

PARAMETER		SYMBOL	MI51TA	MIB51TA	UNIT	CONDITIONS
Radiant Power Output	TYP	Po	5	8	mW	IF=50mA
Forward Voltage	MAX	V_F	1.8	1.8	V	IF=20mA
Reverse Current	MAX	I_R	100	100	μA	VR=5V
Half Intensity Beam Angle	TYP	θ HI	40	70	degree	IF=20mA
Peak Wavelength	TYP	λ ρ	880	880	nm	IF=20mA
Spectrum Line Half Width	TYP	Δ λ	70	70	nm	IF=20mA

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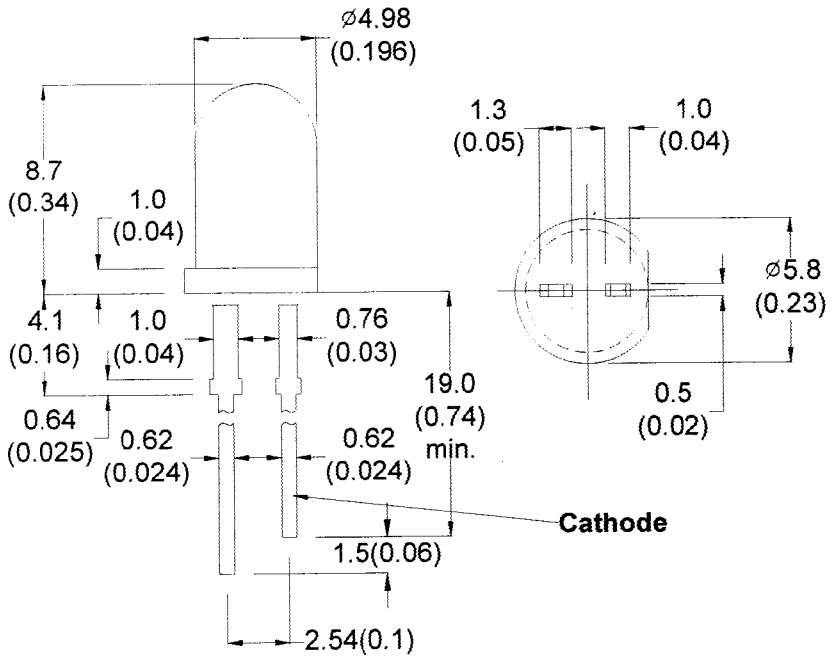
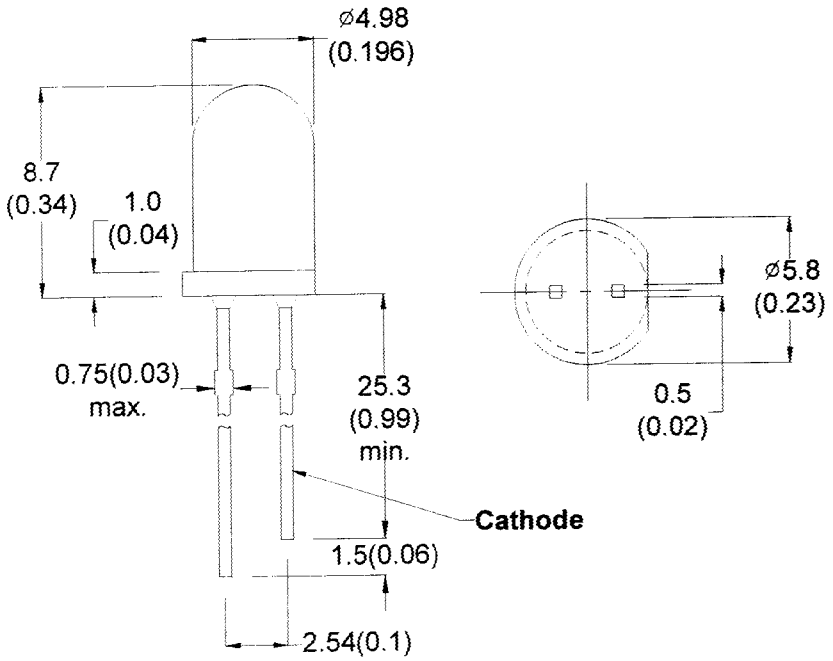
Rev.A

MECHANICAL OUTLINE

MI51TA



MIB51TA



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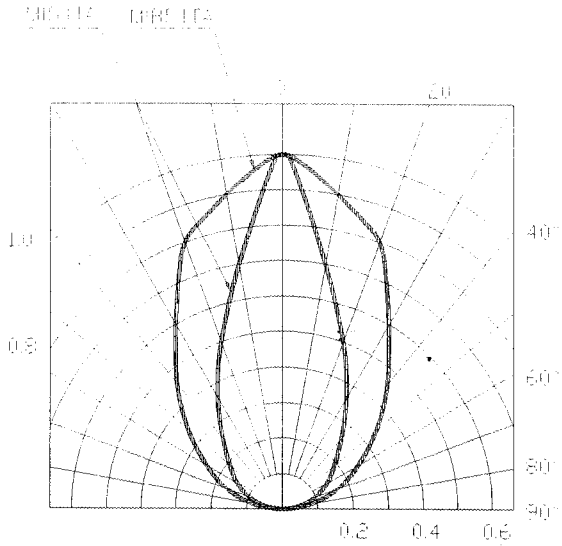
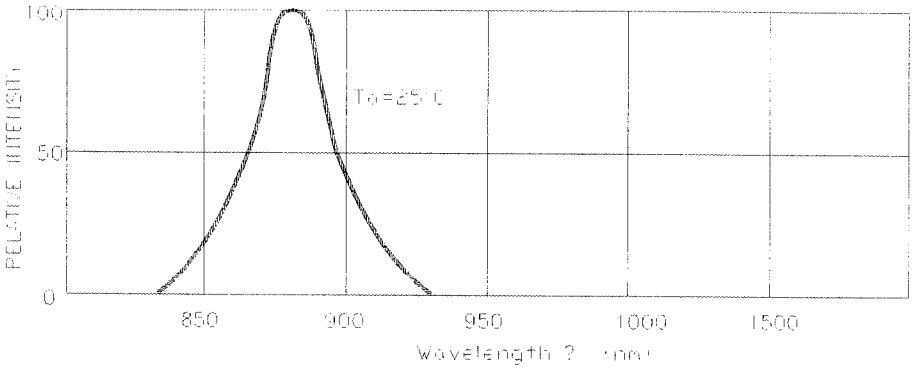
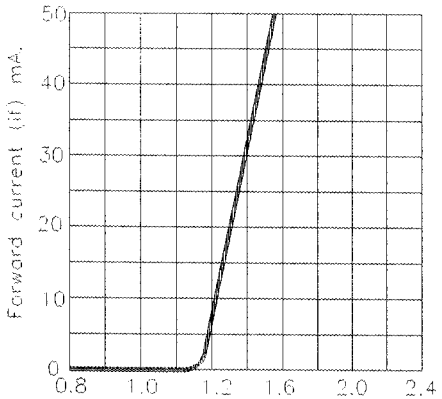


SPATIAL DISTRIBUTION



RELATIVE INTENSITY VS.WAVELENGTH



FORWARD CURRENTS VS.. FORWARD VOLTAGE